



NPN Triple Diffused Planar Silicon Transistor

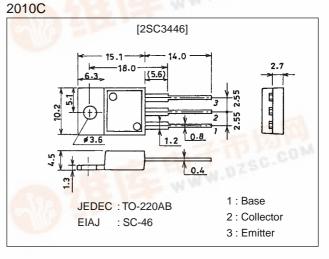


### **Features**

- · High breakdown voltage and high reliability.
- · Fast switching speed ( $t_f : 0.1 \mu s$  typ).
- $\cdot$  Wide ASO.
- · Adoption of MBIT process.

## **Package Dimensions**

## unit:mm



# **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		800	V
Collector-to-Emitter Voltage	VCEO		500	V
Emitter-to-Base Voltage	VEBO		7	V
Collector Current	IC		- 3	А
Collector Current (Pulse)	ICP	PW≤300µs, Duty Cycle≤10%	6	А
Base Current	Ι <sub>Β</sub>		1	А
Collector Dissipation	PC	Tc=25°C	40	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg	10 mil	-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector Cutoff Current	ICBO	V <sub>CB</sub> =500V, I <sub>E</sub> =0			10	μΑ
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =5V, I <sub>C</sub> =0		-	10	μA
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =5V, I <sub>C</sub> =0.3A	15*	- 5	2.2.14	10%
	h <sub>FE</sub> 2	V <sub>CE</sub> =5V, I <sub>C</sub> =1.5A	8		50-	
Gain-Bandwidth Product	fT	V <sub>CE</sub> =10V, I <sub>C</sub> =0.3A	in W	18		MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		50		pF

\*: The h<sub>FE</sub>l of the 2SC3446 is classified as follows. When specifying the h<sub>FE</sub>l rank, specify two ranks or more in principle.

15 L 30 20 M 40 30 N 50

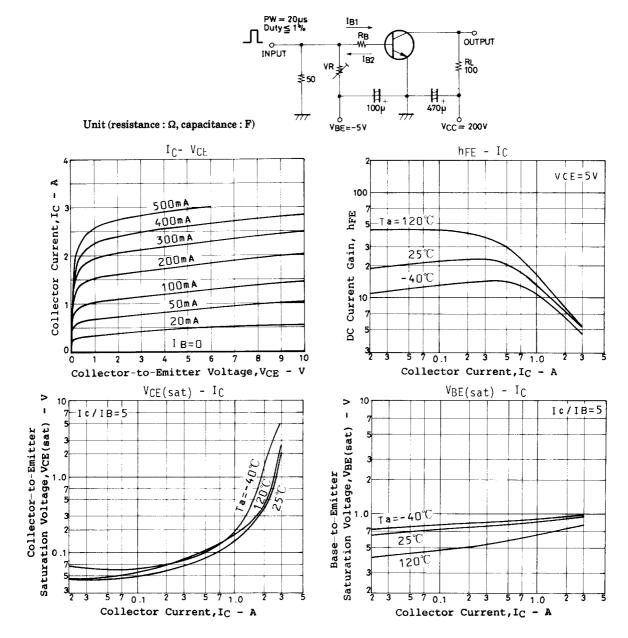
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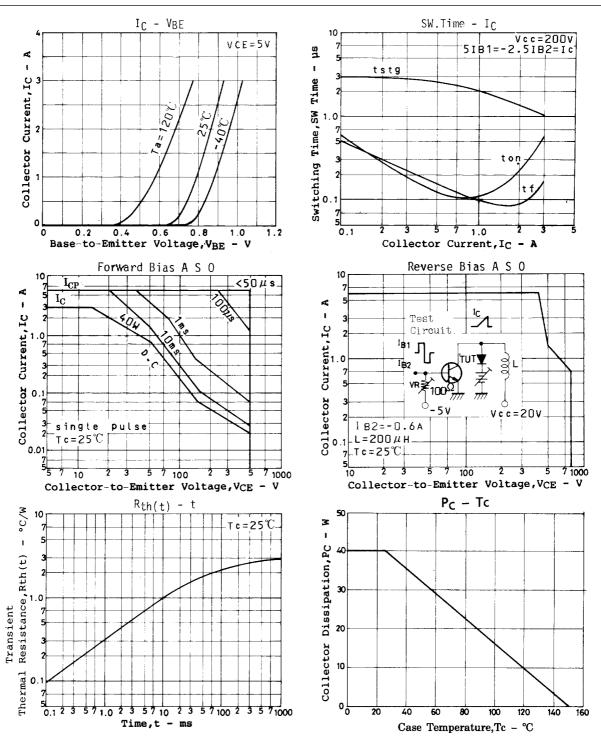
### 2SC3446

Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =1.5A, I <sub>B</sub> =0.3A			1.0	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =1.5A, I <sub>B</sub> =0.3A			1.5	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =1mA, I <sub>E</sub> =0	800			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =5mA, R <sub>BE</sub> =∞	500			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =1mA, I <sub>C</sub> =0	7			V
Collector-to-Emitter Sustain Voltage	V <sub>CEX(sus)</sub>	I <sub>C</sub> =1.5A, I <sub>B1</sub> =-I <sub>B2</sub> =0.6A, L=2mH, clamped	500			V
Turn-ON Time	ton	$V_{CC}$ =200V, 5I <sub>B1</sub> =-2.5I <sub>B2</sub> =I <sub>C</sub> =2A, R <sub>L</sub> =100 $\Omega$			0.5	μs
Storage Time	tstg	$V_{CC}$ =200V, 5I <sub>B1</sub> =-2.5I <sub>B2</sub> =I <sub>C</sub> =2A, R <sub>L</sub> =100 $\Omega$			3.0	μs
Fall Time	t <sub>f</sub>	$V_{CC}$ =200V, 5I <sub>B1</sub> =-2.5I <sub>B2</sub> =I <sub>C</sub> =2A, R <sub>L</sub> =100 $\Omega$			0.3	μs

#### **Switching Time Test Circuit**



2SC3446



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